

wherein a surface zone of the first conductivity type is formed forming forms one of the a first anode and cathode zones area of the SCR element, and

the surface area having has a surface zone of the second conductivity type, further denoted as first zone, situated remote from the well and forming the othera second anode and cathode area of the SCR element, and

the gated diode containing a gate insulated from the surface of the semiconductor body and a highly-doped second conductivity type surface zone aligned to this gate further denoted as second zone, which aligned surface zone partly overlaps the well of the second conductivity type, characterized in that the said second zone stretches out only along a part of the periphery of the well, whereas the first zone is provided along at least another part of this periphery of the well which is free from the said second zone.

4. (Amended) A semiconductor device as claimed in claim 3, characterized in that the said further zone of the second conductivity type and the said first zone of the second conductivity type form a coherent zone of the second conductivity type.